

Dr. Shih-Yen Lin was born in Taiwan on November 11, 1972. He received the B.S. degree in physics from National Taiwan University in 1995, M.S. and Ph.D degrees in electrical engineering from National Taiwan University in 1997 and 2001, respectively. His Ph.D thesis is focused on the characteristics of InAs/GaAs quantum-dot structure and its application in infrared photodetector. He was the deputy of manager of R&D department at Land Mark optoelectronics corp., Tainan, Taiwan during 2001 to 2003. During 2003-2006, he was with Electronics & Optoelectronics Research Laboratories, Industrial Technology Research Institute, Hsinchu, Taiwan. He joined Research Center for Applied Sciences (RCAS), Academia Sinica, Taipei, Taiwan at 2006 as a assistant research fellow. He is also adjunct professors of the Graduate Institute of Electronics Engineering, National Taiwan University, Department of Photonics, National Cheng Kung University, Department of Materials Science and Engineering, National Dong Hwa University and Institute of Optoelectronic Sciences, National Taiwan Ocean University. His research interests focused on the device applications of nano-structures prepared by molecular beam epitaxy (MBE) and 2-D material growth and applications. He is now a associate research fellow at RCAS, Academia Sinica and a senior member of IEEE.

